

Important notice

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Kind regards,

Team Nexperia

BC847 series

45 V, 100 mA NPN general-purpose transistors Rev. 9 — 23 September 2014

Product data sheet

1. **Product profile**

1.1 General description

NPN general-purpose transistors in Surface-Mounted Device (SMD) plastic packages.

Table 1. **Product overview**

Type number[1]	Package		PNP complement	
	NXP	JEITA	JEDEC	
BC847	SOT23	-	TO-236AB	BC857
BC847A				BC857A
BC847B				BC857B
BC847C				BC857C
BC847W	SOT323	SC-70	-	BC857W
BC847AW				BC857AW
BC847BW				BC857BW
BC847CW				BC857CW
BC847T	SOT416	SC-75	-	BC857T
BC847AT				BC857AT
BC847BT				BC857BT
BC847CT				BC857CT
BC847AM	SOT883	SC-101	-	BC857AM
BC847BM				BC857BM
BC847CM				BC857CM

^[1] Valid for all available selection groups.

1.2 Features and benefits

- General-purpose transistors
- SMD plastic packages
- Three different gain selections
- AEC-Q101 qualified

1.3 Applications

General-purpose switching and amplification



1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base		-	-	45	V
I _C	collector current			-	-	100	mA
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 2 \text{ mA}$	[1]	110	-	800	
	h _{FE} group A			110	180	220	
	h _{FE} group B			200	290	450	
	h _{FE} group C	1		420	520	800	

^[1] $T_{amb} = 25$ °C unless otherwise specified

2. Pinning information

Table 3. Pinning

Pin	Description	Simplified outline	Graphic symbol
SOT23, SOT3	323, SOT416		
1	base		
2	emitter	3	3
3	collector	1 2 006aaa144	1
SOT883			
1	base		_
2	emitter	1 3	3
3	collector	2 Transparent top view	12 sym021

3. Ordering information

Table 4. Ordering information

Type number[1]	Package					
	Name	Description	Version			
BC847	-	plastic surface-mounted package; 3 leads	SOT23			
BC847A						
BC847B						
BC847C						
BC847W	SC-70	plastic surface-mounted package; 3 leads	SOT323			
BC847AW						
BC847BW						
BC847CW						
BC847T	SC-75	plastic surface-mounted package; 3 leads	SOT416			
BC847AT						
BC847BT						
BC847CT						
BC847AM	SC-101	leadless ultra small plastic package; 3 solder lands;	SOT883			
BC847BM		body $1.0 \times 0.6 \times 0.5$ mm				
BC847CM						

^[1] Valid for all available selection groups.

4. Marking

Table 5. Marking codes

Type number	Marking code[1]	Type number	Marking code[1]
BC847	1H*	BC847T	1N
BC847A	1E*	BC847AT	1E
BC847B	1F*	BC847BT	1F
BC847C	1G*	BC847CT	1G
BC847W	1H*	BC847AM	D4
BC847AW	1E*	BC847BM	D5
BC847BW	1F*	BC847CM	D6
BC847CW	1G*		

^{[1] * =} placeholder for manufacturing site code

5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	50	V
V_{CEO}	collector-emitter voltage	open base		-	45	V
V_{EBO}	emitter-base voltage	open collector		-	6	V
Ic	collector current			-	100	mA
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$		-	200	mA
I _{BM}	peak base current	single pulse; $t_p \le 1 \text{ ms}$		-	100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	<u>[1]</u>			
	SOT23			-	250	mW
	SOT323			-	200	mW
	SOT416			-	150	mW
	SOT883		[2]	-	250	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	+150	°C
T _{stg}	storage temperature			-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]				
	SOT23			-	-	500	K/W
	SOT323			-	-	625	K/W
	SOT416			-	-	833	K/W
	SOT883		[2]	-	-	500	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[2] Device mounted on an FR4 PCB with 60 μm copper strip line, standard footprint.

^[2] Device mounted on an FR4 PCB with 60 μm copper strip line, standard footprint.

7. Characteristics

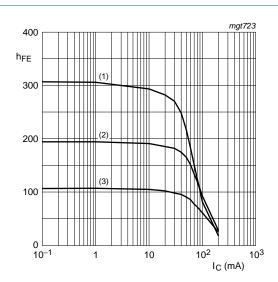
Table 8. Characteristics

 $T_{amb} = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = 30 V; I _E = 0 A		-	-	15	nA
	current	$V_{CB} = 30 \text{ V}; I_E = 0 \text{ A};$ $T_j = 150 \text{ °C}$		-	-	5	μА
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A		-	-	100	nA
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 10 \mu\text{A}$					
	h _{FE} group A			-	170	-	
	h _{FE} group B			-	280	-	
	h _{FE} group C			-	420	-	
	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 2 \text{ mA}$		110	-	800	
	h _{FE} group A			110	180	220	
	h _{FE} group B			200	290	450	
	h _{FE} group C			420	520	800	
V_{CEsat}	collector-emitter	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$		-	90	200	mV
	saturation voltage	$I_C = 100 \text{ mA}; I_B = 5 \text{ mA}$	<u>[1]</u>	-	200	400	mV
V_{BEsat}	base-emitter	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	[2]	-	700	-	mV
	saturation voltage	$I_C = 100 \text{ mA}; I_B = 5 \text{ mA}$	[2]	-	900	-	mV
V_{BE}	base-emitter voltage	$I_C = 2 \text{ mA}; V_{CE} = 5 \text{ V}$	[2]	580	660	700	mV
		$I_C = 10 \text{ mA}; V_{CE} = 5 \text{ V}$		-	-	770	mV
f _T	transition frequency	$V_{CE} = 5 \text{ V; } I_{C} = 10 \text{ mA;}$ f = 100 MHz		100	-	-	MHz
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz		-	-	1.5	pF
C _e	emitter capacitance	$V_{EB} = 0.5 \text{ V}; I_C = I_c = 0 \text{ A};$ f = 1 MHz		-	11	-	pF
NF	noise figure	$\begin{split} I_C &= 200 \; \mu\text{A}; \; V_{CE} = 5 \; V; \\ R_S &= 2 \; k\Omega; \; f = 1 \; k\text{Hz}; \\ B &= 200 \; \text{Hz} \end{split}$		-	2	10	dB

^[1] Pulse test: $t_p \le 300~\mu s;~\delta = 0.02.$

^[2] V_{BE} decreases by approximately 2 mV/K with increasing temperature.



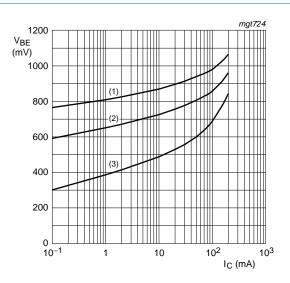
$$V_{CE} = 5 V$$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig 1. Group A: DC current gain as a function of collector current; typical values



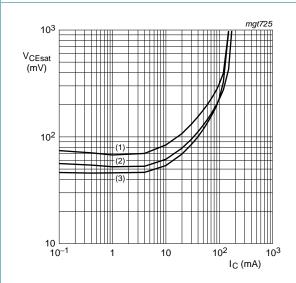
$$V_{CE} = 5 V$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = 150 \, ^{\circ}C$

Fig 2. Group A: Base-emitter voltage as a function of collector current; typical values



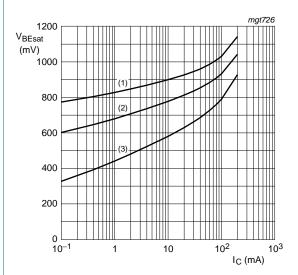
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 3. Group A: Collector-emitter saturation voltage as a function of collector current; typical values



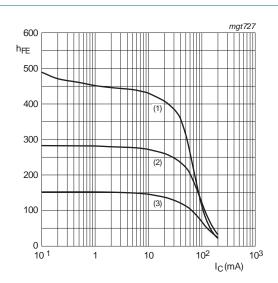
$$I_{\rm C}/I_{\rm B} = 10$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = 150 \, ^{\circ}C$

Fig 4. Group A: Base-emitter saturation voltage as a function of collector current; typical values



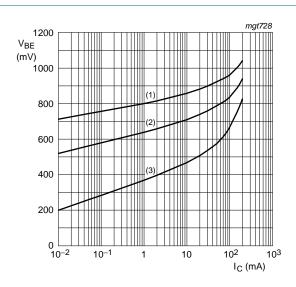
$$V_{CE} = 5 V$$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig 5. Group B: DC current gain as a function of collector current; typical values



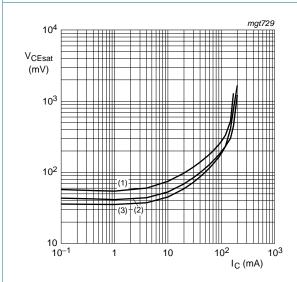
$$V_{CE} = 5 \text{ V}$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 150 \, ^{\circ}C$$

Fig 6. Group B: Base-emitter voltage as a function of collector current; typical values



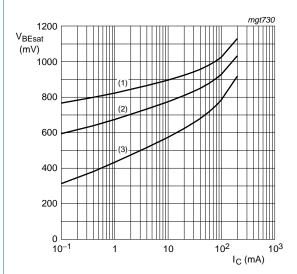
 $I_{\rm C}/I_{\rm B} = 20$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig 7. Group B: Collector-emitter saturation voltage as a function of collector current; typical values



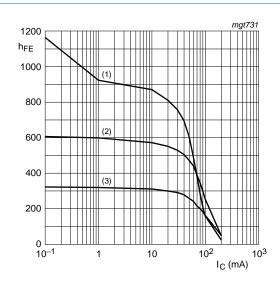
$$I_{\rm C}/I_{\rm B} = 10$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = 150 \, ^{\circ}C$

Fig 8. Group B: Base-emitter saturation voltage as a function of collector current; typical values



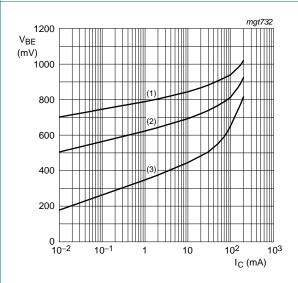
$$V_{CE} = 5 V$$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig 9. Group C: DC current gain as a function of collector current; typical values



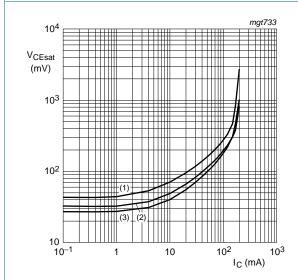
$$V_{CE} = 5 \text{ V}$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = 150 \, ^{\circ}C$

Fig 10. Group C: Base-emitter voltage as a function of collector current; typical values



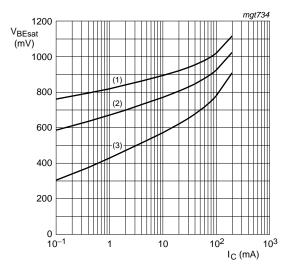
 $I_{\rm C}/I_{\rm B} = 20$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig 11. Group C: Collector-emitter saturation voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 10$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = 150 \, ^{\circ}C$

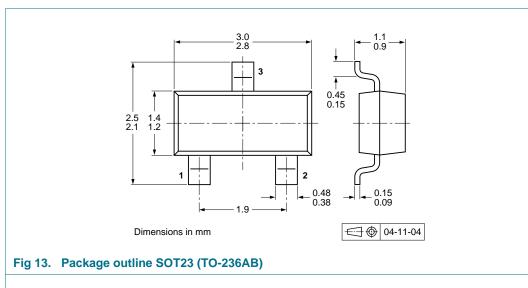
Fig 12. Group C: Base-emitter saturation voltage as a function of collector current; typical values

8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



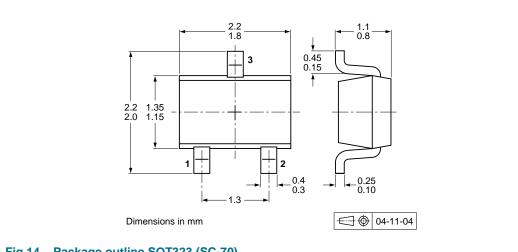
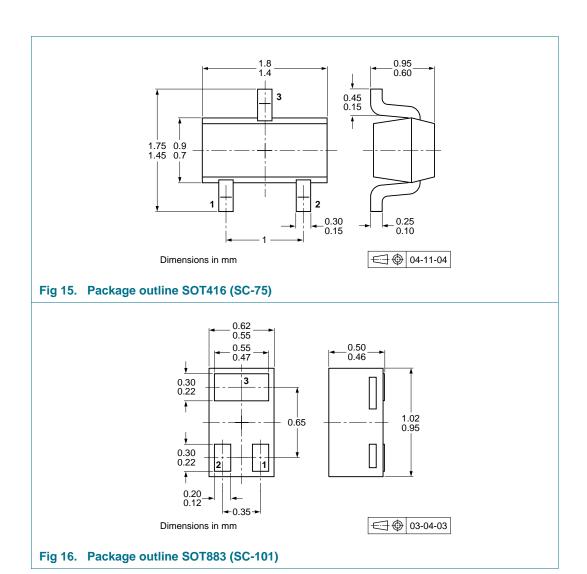
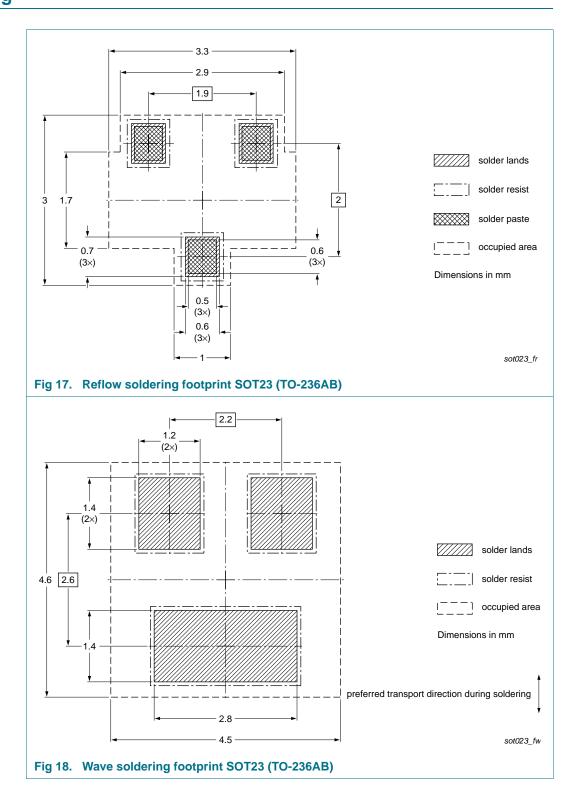
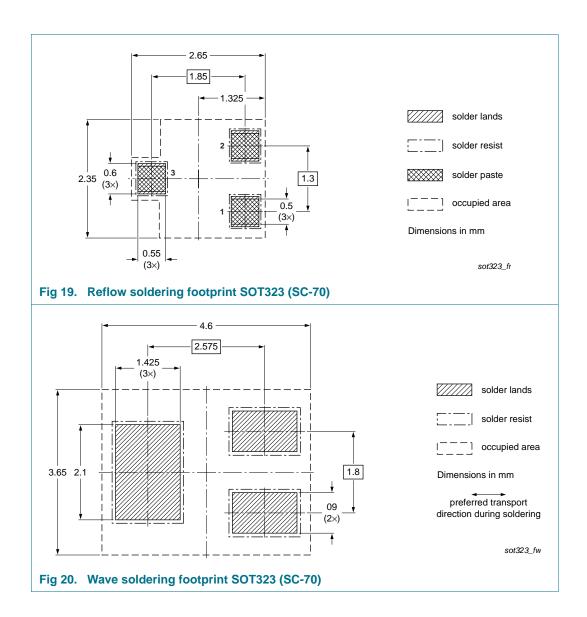


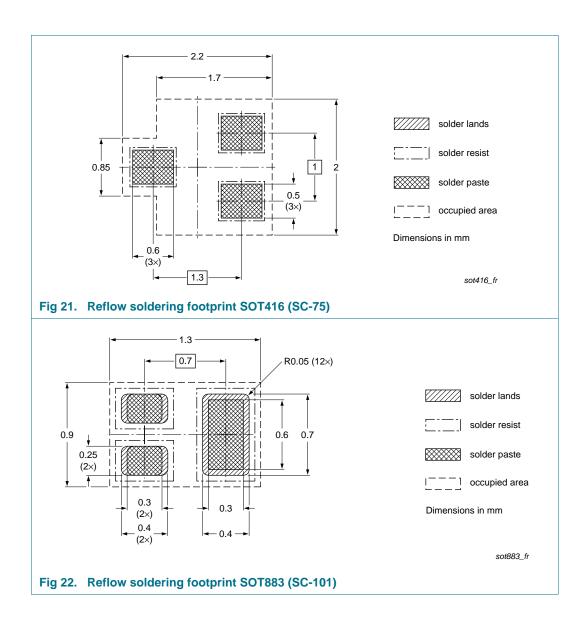
Fig 14. Package outline SOT323 (SC-70)



10. Soldering







11. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
BC847_SER v.9	20140923	Product data sheet	-	BC847_SER v.8	
Modifications:	 Section 1.2 "Features and benefits": updated 				
	Section 5 "L	imiting values": updated			
	• Figure 5: co	rrected			
	 Section 8 "T 	est information": added			
	Section 12 "	Legal information": updated	b		
BC847_SER v.8	20120820	Product data sheet	-	BC847_BC547_SER v.7	
BC847_BC547_SER v.7	20081210	Product data sheet	-	BC847_BC547_SER v.6	
BC847_BC547_SER v.6	20050519	Product data sheet	-	-	

NXP Semiconductors BC847 series

45 V, 100 mA NPN general-purpose transistors

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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BC847_SER

NXP Semiconductors BC847 series

45 V, 100 mA NPN general-purpose transistors

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BC847 series

45 V, 100 mA NPN general-purpose transistors

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